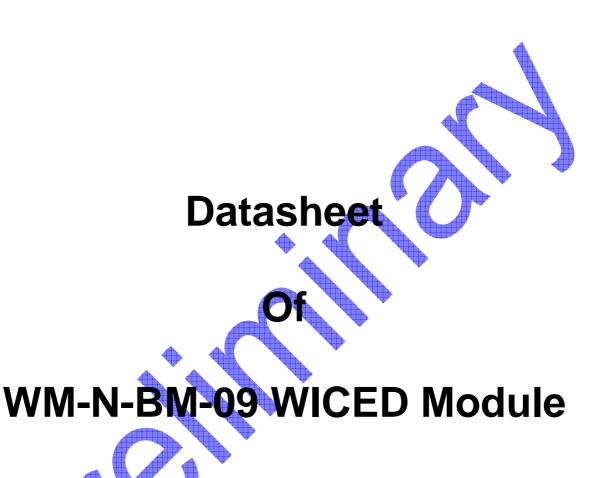
## 802.11b/g/n SiP Module (WM-N-BM -09)



Data Sheet Nov. 14 2013 Rev. 2.4

www.usi.com.tw



#### Introduction

The WM-N-BM-09 wireless SiP module which refers as "SiP module" is a small size module and consists of a Broadcom BCM43362 single-chip, a ST STM32F205 MCU. The WM-N-BM-09 provides for the highest level integration for electronic accessories on WICED licensing, featuring integrated IEEE 802.11b/g and handheld device class 802.11n.

It includes a 2.4 GHz WLAN CMOS power amplifier (PA) that meets the output power requirements of most handheld systems. An optional external low-noise amplifier (LNA) and external PA are also supported. Along with the integrated power amplifier, the WM-N-BM-09 also includes integrated transmit and receive baluns, further reducing the overall solution cost.

The small size & low profile physical design make it easier for system design to enable high performance wireless connectivity without space constrain. This multi- functionality and board to board physical interface provides SPI/USB/UART interface options.

Hardware WAPI acceleration engine, AES, TKIP, WPA and WPA2 are supported to provide the latest security requirement on your network.

For the software and driver development, USI provides extensive technical document and reference software code for the system integration under the agreement of Broadcom International Ltd.

Hardware evaluation kit and development utilities will be released base on listed OS and processors to OEM customers.

#### **Features**

#### BCM43362 Wi-Fi

- Single band 2.4GHz IEEE 802.11b/g/n
- Supports wireless data rates up to 65Mbit/s
- Integrated RF power amplifier



#### STM32F205RGY6 Microprocessor

- ARM 32-bit Cortex-M3 CPU
- CPU frequency up to 120MHz
- 1 MB Flash memory
- 128 kB SRAM
- Low-power sleep, standby and stop modes

#### WM-N-BM-09 Wireless Sip Module

- Featuring integrated IEEE 802.11 b/g/n.
- Supports per packet Rx Antenna diversity
- Low power consumption & excellent power management performance extend battery life.
- Small size suitable for low volume system integration.
- Easy for integration into mobile and handheld device with flexible system configuration.
- 2.412-2.484 GHz two SKUs for worldwide market.
- Lead Free design which supporting Green design requirement, RoHS Compliance.



## **Device Package**

• 11x12 mm LQFP 58 pin

	Change Sheet						
Rev.	Date	Descript	tion of	change	Approval & Date		
		Page	Par	Change(s)			
2.1	12/10/25	All	All	Release version	Kevin / Scarrie		
2.2	13/03/07	14	14	Update Metal shielding type	Jas <mark>on</mark>		
2.3	13/05/13	9	9	Modify operating high temp to 70 degrees	Jason		
2.4	13/11/14	9	9	Modify operating high temp to 85°C	Donny		
					•		

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#### 1. EXECUTIVE SUMMARY

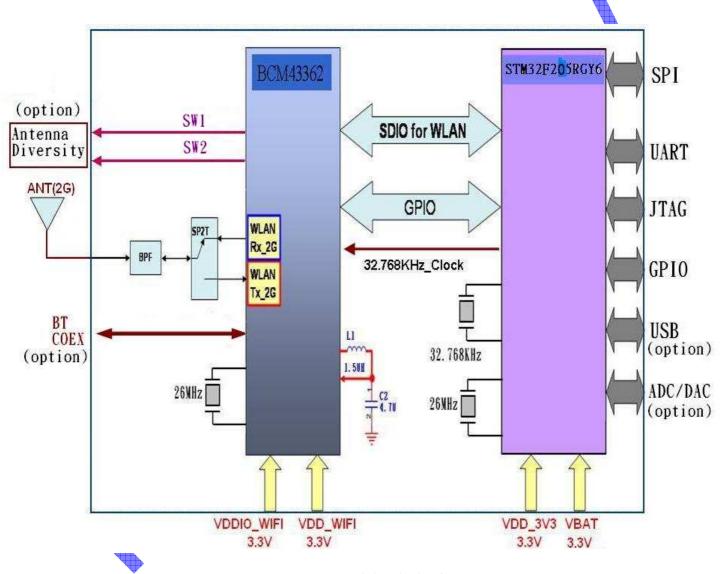
The WM-N-BM-09 module - is one of the product families in UG's product offering, targeting for system integration requiring a smaller form factor. It also provides the standard migration to high data rate to UG's current SIP customers.

The purpose of this document is to define the product specification for 802.11b/g/n (draft n) WiFi module WM-N-BM-09. All the data in this document is based on Broadcom 43362 data sheet , STM32F205xx datasheet and other documents provided from Broadcom and ST . The data will be updated after implementing the measurement of the module.



#### 2. BLOCK DIAGRAM

The WM-N-BM-09 module is designed based on Broadcom 43362 chipset and ST MCU solution. It supports generic SPI, UART, USB interface to connect the WLAN to the host processor. A simplified block diagram of the WM-N-BM-09 module is depicted in below Figure.



WM-N-BM-09 Module Block Diagram

#### 3. DELIVERABLES

The following products and software will be part of the product.

- WM-N-BM-09 Module with packaging
- Evaluation kits (with SPI / UART / USB interface)
- Software utility which supporting customer for integration, performance test and homologation. Capable of testing, loading (firmware) and configuring (MAC, CIS) for the WM-N-BM-09 module.
- Unit Test / Qualification report
- Product Specifications.
- Agency certification pre-test report base on adapter boards



#### 4. REFERENCE DOCUMENTS

C.I.S.P.R. Pub. 22	"Limits and methods of measurement of radio interference characteristics of information technology equipment." International Special Committee on Radio Interference (C.I.S.P.R.), Third Edition, 1997.
CB Bulletin No. 96A	"Adherence to IEC Standards: "Requirements for IEC 950, 2 <sup>nd</sup> Edition and Amendments 1 (1991), 2(1993), 3 (1995) and 4(1996). Product Categories: Meas, Med, Off, Tron." IEC System for Conformity Testing to Standards for Safety of Electrical Equipment (IECEE), April 2000.
CFR 47, Part 15-B	"Unintentional Radiators". Title 47 of the Code of Federal Regulations, Part 15, FCC Rules, Radio Frequency Devices, Subpart B.
CFR 47, Part 15-C	"Intentional Radiators". Title 47 of the Code of Federal Regulations, Part 15, FCC Rules, Subpart C. URL: <a href="http://www.access.gpo.gov/nara/cfr/waisidx">http://www.access.gpo.gov/nara/cfr/waisidx</a> 98/47cfr15 98.html
CSA C22.2 No. 950-95	"Safety of Information Technology Equipment including Electrical Business Equipment, Third Edition." Canadian Standards Association, 1995, including revised pages through July 1997.
EN 60 950	"Safety of Information Technology Equipment Including Electrical Business Equipment." European Committee for Electrotechnical Standardization (CENELEC), 1996, (IEC 950, Second Edition, including Amendment 1, 2, 3 and 4).
IEC 950	"Safety of Information Technology Equipment Including Electrical Business Equipment." European Committee for Electrotechnical Standardization, Intentional Electrotechnical Commission. 1991, Second Edition, including Amendments 1, 2, 3, and 4.
IEEE 802.11	"Wireless LAN Medium Access Control (MAC) And Physical Layer (PHY) Specifications." Institute of Electrical and Electronics Engineers. 1999.

#### 5. TECHNICAL SPECIFICATION

#### **5.1 ABSOLUTE MAXIMUM RATING**

Max +3.6 Volt	
- 40° to 85° Celsius	
+/- 2%	Max. Values not exceeding Operating voltage
	- 40° to 85° Celsius

#### 5.2 RECOMMEND OPERATION CONDITION

#### **TEMPERATURE, HUMIDITY**

The WM-N-BM-09 module has to withstand the operational requirements as listed in the table below.

Operating Temperature	-20° to 85° Celsius	
Humidity range	Max 95%	Non condensing, relative humidity

The maximum operating ambient temperature range can up to 85degC, but exposure to absolute-maximum-rated conditions may cause performance degradation and affect device reliability.

#### **VOLTAGE**

Power supply for the WM-N-BM-09 module will be provided by the host via the power pins

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD_WIFI	Power Supply for BCM43362	3.0	3.3	3.6	V
VDDIO_WIFI	Host Interface Power Supply	3.0	3.3	3.6	V
VBAT	Backup operating voltage	3.0	3.3	3.6	V
VDD_3V3	Power Supply for MCU	3.0	3.3	3.6	V

## **CURRENT CONSUMPTION**

The WM-N-BM-09 on TX mode Output current Consumption:

(Typical spec is defined @3.3V 25°C; MAX. spec is defined @3.0V 60°C)

Current Consumption	TYP.	MAX.
Tx output power @16.5 dBm on 11b 1M	365 mA	430 mA
Tx output power @ 16.5 dBm on 11b 11M	360 mA	430 mA
Tx output power @ 15 dBm on 11g 6M	330 mA	380 mA
Tx output power @ 13 dBm on 11g 54M	270 mA	320 mA
Tx output power @ 14.5 dBm on 11n MCS0	310 mA	360 mA
Tx output power @ 12 dBm on 11n MCS7	235 mA	280 mA

The WM-N-BM-09 on RX mode current Consumption:

(Typical spec is defined @3.3V 25 $^{\circ}$ C ; MAX. spec is defined @3.0V 60 $^{\circ}$ C)

Current Consumption	TYP.	MAX.
Rx @ 11b 1M	120 mA	150 mA
Rx @ 11b 11M	120 mA	1 <mark>5</mark> 0 mA
Rx @ 11g 6M	120 mA	150 mA
Rx @ 11g 54M	120 mA	150 mA
Rx @ 11n MCS0	120 mA	150 mA
Rx @ 11n MCS7	120 mA	150 mA

#### **5.3 WIRELESS SPECIFICATIONS**

The WM-N-BM-09 module complies with the following features and standards;

Features	Description
WLAN Standards	IEEE 802 11b/g/n
Antenna Port	Single Antenna
Frequency Band	2.400 GHz – 2.484 GHz
Number of Sub Channels	1~ 14 Channels
Modulation	DSSS, CCK, OFDM, BPSK, QPSK,16QAM, 64QAM
Supported data rates	1, 2, 5.5, 11 (Mbps)
	6, 9, 12, 18, 24, 36, 48, 54 (Mbps)
	HT20_MCS0(6.5Mbps) ~ HT20_MCS7(65Mbps)

#### 5.4 SPECIFICATIONS OF WIFI'S OUTPUT POWER . EVM . SENSITIVITY

The WM-N-BM-09 module WiFi output power as list in the table below:

Characteristics		TYP.	Criteria	Unit
	1M	16.5	+/- 1.5	dBm
RF Average Output Power, 802.11b CCK Mode	11M	16.5	+/- 1.5	dBm
	6M	15	+/- 1.5	dBm
RF Average Output Power, 802.11g OFDM Mode	54M	13	+/- 1.5	dBm
	MCS0	14.5	<del>-</del> /- 1.5	dBm
RF Average Output Power, 802.11n OFDM Mode	MCS7	12	+/- 1.5	dBm

WiFi TX EVM follow the IEEE spec that as list in the table below:

Characteristics		IEEE Spec	Unit
RF Average Output EVM (11b)	@1 Mbps	-10	dB
Ki Average Odiput Evivi (11b)	@11 Mbps	-10	dB
RF Average Output EVM (11g)	@6 Mbps	-5	dB
RF Average Output EVM (11g)	@54 Mbps	-25	dB
RF Average Output EVM (11n)	@ MCS0	-5	dB
IN Average Output Lyw [111]	@ MCS7	-28	dB

The WM-N-BM-09 module WiFi Sensitivity as list in the table below:

Receiver Characteristics	TYP.	MAX.	Unit
PER <8%, Rx Sensitivity @ 1 Mbps	-96	-89	dBm
PER <8%, Rx Sensitivity @ 11 Mbps	-88	-84	dBm
PER <10% Rx Sensitivity @ 6 Mbps	-90	-83	dBm
PER <10%, Rx Sensitivity @ 54 Mbps	-74	-70	dBm
PER <10%, Rx Sensitivity @ MCS0	-89	-83	dBm
PER <10%, Rx Sensitivity @ MCS7	-71	-67	dBm

#### 6. FLASH MEMORY

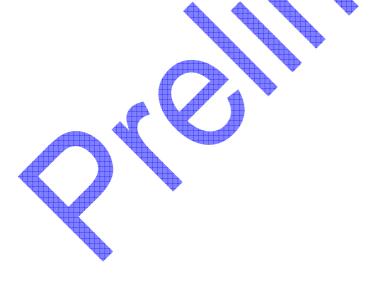
#### 6.1 MCU EMBEDDED FLASH MEMORY

The STM32F205RG devices embed a 128-bit wide Flash memory of 1 Mbytes available for storing programs and data. It also features 512 bytes of OTP memory that can be used to store critical user data such as Ethernet MAC addresses or cryptographic keys.

For information on programming, erasing and protection of the internal Flash memory, please refer to the STM32F205RG Flash programming manual. The reference and Flash programming manuals are both available from the STMicroelectronics website www.st.com.

#### 6.2 EXTERNAL FLASH MEMORY

WM-N-BM-09 provide the option that user can external flash. SPI interface pin via to flash. The STM32F205RG software is feature compatible. It allow user to run different memory densities and peripherals for a greater degree of freedom during the development cycle.



#### 7. I/O PORT CHARACTERISTICS

Unless otherwise specified, the parameters given as below table.

For detail information of I/O injection parameters and conditions, please refer to STM32F205RG I/O manual.

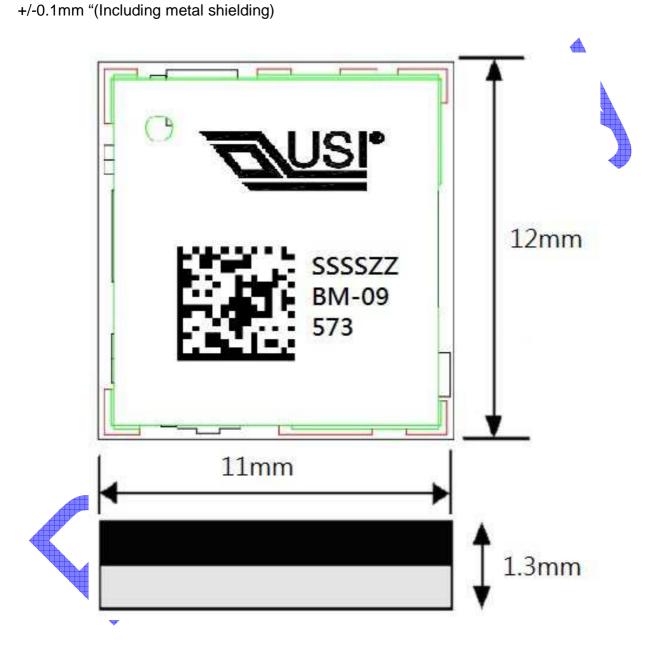
Table 7.1 I/O static characteristics

					A 184		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V	Standard IO input low level voltage		-0.3		0.28*(V <sub>DD</sub> -2 V)+0.8 V	٧	
V <sub>IL</sub>	IO FT <sup>(1)</sup> input low level voltage		-0.3		0.32*(V <sub>DD</sub> -2 V)+0.75 V	٧	
	Standard IO input high level voltage		0.41*(V <sub>DD</sub> -2 V)+1.3 V		V <sub>DD</sub> +0.3	٧	
VIH	IO FT <sup>(1)</sup> input high level	V <sub>DD</sub> > 2 V	0.40*/V 0.10+4.V		5.5	· v	
	voltage	$V_{DD} \le 2 V$	0.42*(V <sub>DD</sub> -2 V)+1 V		5.2	v	
V <sub>hys</sub>	Standard IO Schmitt trigger voltage hysteresis <sup>(2)</sup>		200			mV	
IO FT Schmitt trigger voltage hysteresis <sup>(2)</sup>			5% V <sub>DD</sub> <sup>(3)</sup>			mV	
I <sub>lkg</sub> Input leakage current <sup>(4)</sup>		V <sub>SS</sub> ≤V <sub>IN</sub> ≤V <sub>DD</sub> Standard I/Os			±1	μА	
		V <sub>IN</sub> = 5 V, I/O FT			3		
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(5)</sup>	V <sub>IN</sub> = V <sub>SS</sub>	30	40	50	kΩ	
R <sub>PD</sub>	Weak pull-down equivalent resistor <sup>(5)</sup>	V <sub>IN</sub> = V <sub>DD</sub>	30	40	50	kΩ	
C <sub>IO</sub>	I/O pin capacitance			5		pF	

- 1. FT = Five-volt tolerant. In order to sustain a voltage higher than VDD+0.3 the internal pull-up/pull-down resistors must be disabled.
- 2. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization, not tested in production.
- 3. With a minimum of 100 mV.
- 4. Leakage could be higher than max. if negative current is injected on adjacent pins.
- 5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This MOS/NMOS contribution to the series resistance is minimum (~10% order).

#### 8. MODULE DIMENSIONS

The WM-N-BM-09 module size and thickness is "12 mm (W) x 11 mm (L) x 1.3 mm (H)



## 9. PIN DESCRIPTION

Pin Out			(	
5 6 1 4 1 3	12 11 10 9	8 7 6	5 4 3 2	1 55
1 5				5 4
1 6				5 3
17	6 1	6 0	5 9	5 2
18				5 1
19				5 0
20				4 9
21	6 4	6 3	6 2	4 8
22				47
23				4 6
2 4	6.7	6 6	6 5	4 5
2.5				4 4
2 6				4 3
27				4 2
57 28 29	3 0 3 1 3 2 3 3	3 4 3 5 3 6	37 38 39 40	4 1 5 8

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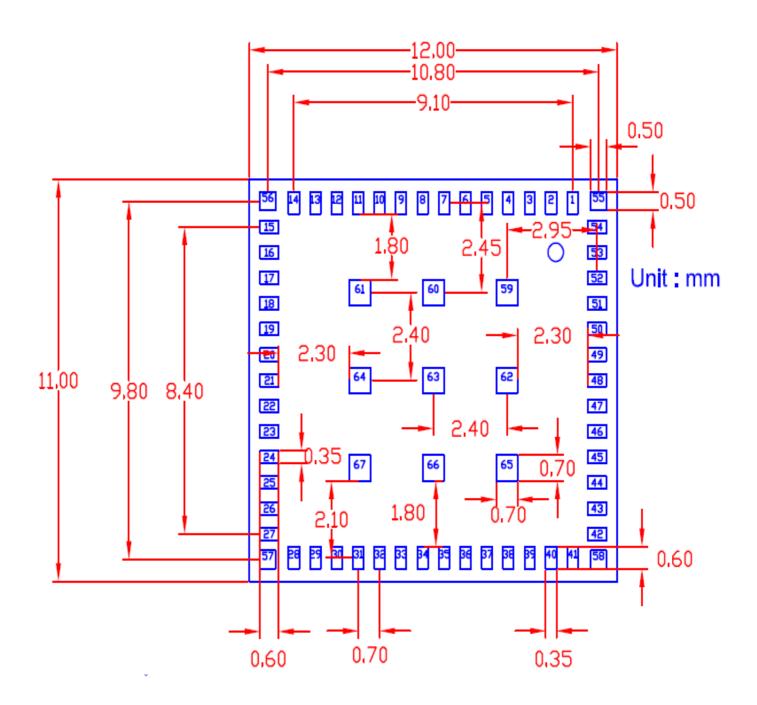
**TOP View** 

#### **Pin Description**

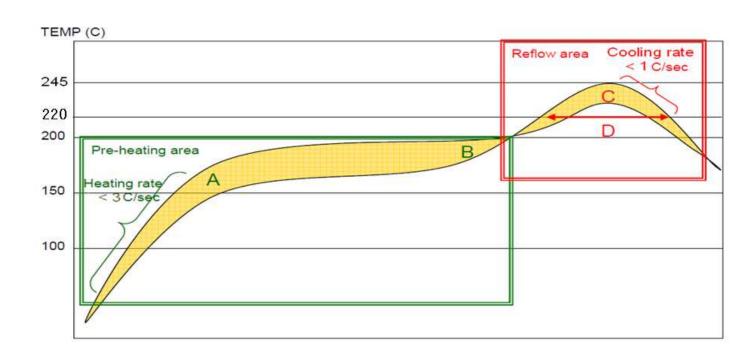
Pin-Number	Pin-Define	Type	Description
1	MICRO_GPIO_7	I/O	GPIO pin
2	MICRO_GPIO_6	I/O	GPIO pin
3	MICRO_GPIO_5	I/O	GPIO pin
4	MICRO_GPIO_4	I/O	GPIO pin
5	MICRO_GPIO_3	I/O	GPIO pin
6	MICRO_GPIO_2	I/O	GPIO pin
7	MICRO_GPIO_1	I/O	GPIO pin
8	MICRO_GPIO_0	I/O	GPIO pin
9	BTCX_RF_ACTIVE	Ι	Coexistence signal indicating that Bluetooth is active.
10	BTCX_STATUS	Ι	Coexistence signal indicating Bluetooth priority status and TX/RX direction.
11	BTCX_TXCONF	Ο	Coexistence output giving Bluetooth permission to transmit.
12	RF_SW_CTRL3_ANT1	Ο	RF switch control line. Default at this pin is low.
13	RF_SW_CTRL0_ANT0	O	RF switch control line. Default at this pin is high
14	GND		Ground
15	ANT	ĬΌ	Antenna port for WLAN
16	GND	-	Ground
17	GND	-4	Ground
18	GND	<b>*CEED</b>	Ground
19	VDD_WIFI	I	Battery voltage input for CBUCK
20	VDD_WIFI	I	Battery voltage input for CBUCK
21	GND		Ground
22	MICRO_SPI_SSN	I/O	SPI_SS
23	MICRI_SPI_MOSI	I/O	SPI_MOSI
24	MICRO_SPI_SCK	I/O	SPI_SCK
25	MICRO_SPI_MISO	I/O	SPI_MISO
26	MICRO_RST_N	I/O	MCU Reset
27	MICRO_WKUP	I/O	MCU-Wake UP

Pin-Number	Pin-Define	Туре	Description
28	VBAT	Ι	MCU operating voltage input (power supply for RTC, external clock, 32 kHz oscillator and backup registers (through power switch) when VDD is not present.)
29	GND		Ground
30	GND		Ground
31 ~ 36	NC		NC
37	GND		Ground
38	MICRO_UART_RX	I/O	UART_RX
39	MICRO_UART_TX	I/O	UART_TX
40	MICRO_JTAG_TCK	I/O	JTAG_TCK
41	MICRO_JTAG_TDO	I/O	JTAG_TDO
42	MICRO_JTAG_TRSTN	I/O	JTAG_TRSTN
43	MICRO_JTAG_TDI	I/O	JTAG_TDI
44	MICRO_JTAG_TMS	I/O	JTAG_TMS
45	GND		Ground
46	VDD_3V3		MCU operating voltage input
47	VDD_3V3		MCU operating voltage input
48	GND		Ground
49	VDDIO_WIFI		Battery voltage input for band-gap and LDOP3
50	GND	<del>-</del>	Ground
51	MICRO_USB_HS_DP	<b>I</b> /O	USB_HS_DP
52	MICRO_USB_HS_DN	I/O	USB_HS_DN
53	MICRO_GPIO_9	I/O	GPIO pin
54	MICRO_GPIO_8	I/O	GPIO pin
55	GND		Ground
56	GND		Ground
57	GND		Ground
58	GND		Ground
59 ~ 67	GND	1	Ground

#### 10. MODULE DIMENSION



## 11. RECOMMEND REFLOW PROFILE

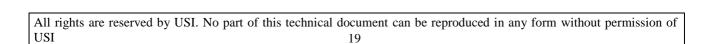


A-B. Temp.: 150~200°C; soak time:60~120sec.

C. Peak temp: 235~245°C

D. Time above 220  $^{\circ}$ C: 40~90sec.

Suggestion: Optimal cooling rate is <1  $^{\circ}$ C/sec. from peak to 220  $^{\circ}$ C.



#### 12. PACKAGE AND STORAGE CONDITION

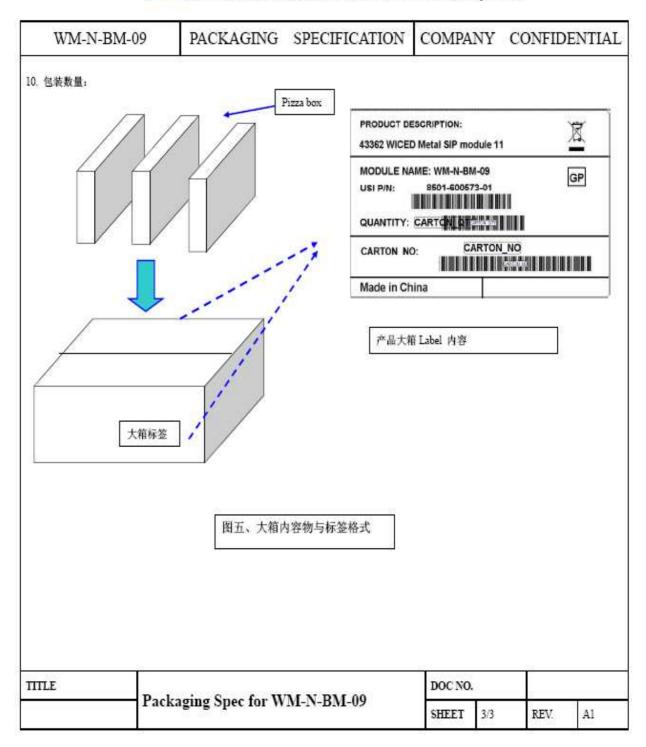
## Universal Scientific Industrial Co., Ltd.

WM-N-BM-09 PACKAGING S					SPECI	PECIFICATION CO			NY	CO	NFIDE	ENTIAI		
Project Name: WM-N-BM-09 Descrip				iption:	otion: 43			3362 WICED Metal SIP module 11						
适用之产品: 8501-600573-01 Tape Ca			Carrier 之	之单元格尺寸: 长 11.4*宽 12.4			2.4*高 1	*高 1.7*PITCH 16(mm)						
MSL information: LEVEL: 3 温度(°C					°C):	250	时间(hour):			168				
使用之包装材	料:					-		_			1		_	
NO	品名					P/N		用量	用量(以大箱计)			用量/pcs		
1	大 箱[	[360*140	*360MM	1]		59-012	2485-11	1	1			0.000223		
2	Pizza	盒[340x3	336x40N	IM]		59-154	1014-12	3			0.000667			
3	产品	标 签(F	Reel/Bag	Box)		59-456	3702-01	9	9			0.002		
4	CARR	RIER TAF	PE(载带)	[100M/F	REEL]	59-306	3474-01	总七	€ 100M		0.0	1666M		
5	COVE	R TAPE	(透明带	步)[300M	/Reel]	59-730	0566-01	105	5M		0.0175M			
6	REEL	(载带滚	动条)			59-303	3164-01	3			0.000667			
7	Protect		and( 保	护护	带 )[1	59-732	2267-01	3	3			0.000667		
8	铝箔	密封组	ž			59-350	0332-01	3	3			0.000667		
9	干燥	燥剂 (66g)(CoCl2 Free)					3005-00	3			0.000667			
10	大 箱	标 签				59-456	3703-01	2			0.000445			
11	湿度	度指示卡(CoCl2 Free)				59-20	1004-01	3	3			0.000667		
12	MSL L	_ABEL(活	等级卷标	₹)	59-52	5934-11	3			0.000667				
先預留 2. 包装时7 3. 在 1500 4. 在卷带) 5. 在 REE 6. 每一铝剂 以真空 7. 每一个4 8. 将已真空	10 格空格 产品的铁品 DPCS 后,再络袋 后,再络袋 汽车。 包装机将线 包装密封线 管包装 Re	片后开始成 差朝上放力 背预留 10 保护带 59 是及纸盒 26 59-35033 袋口密封, 袋上须加贝 eel 放入(5	定品,每标 个 carrier, 格空格, -732090-1 作贴上一引 2-01)放入 如(图二 站一张 MS 9-154014	序放 1PC: 定位符 产品卷装 D1 圈于 F 长 59-456 、一卷产品 )。 GL 标签(F I-12) PIZ	S。 号朝向 后用 C Reel 之 702-01 品、一包 P/N:59- ZA BO	carrier 定 OVER TA 外围,并 (空白标 干燥剂(P 525934-1 X 内,每	位孔(图一) APE 再多绕 以美纹胶黏 签 PN: 59 /N 59-3930 1)在 ATTE 大箱放 3 盒	,每 一圈, 贴固。 -5141 005-00 NTIO :产品,	Tape)装上ta	500PC: 胶带固 标签( 湿度指 另内容如	S。 定。 图二) 示卡(	)。 P/N 59-2 l)所示。	01004-01	
图一、产品	品放置方向	ij			Pin	PRESENT.	550 to 1 MALOS	/	7 -	Use	r Feed	Direction		
TITLE	g.	Packa	ging S	pec for	r WM	1-N-BN	M-09		DOC NO	1/3		REV.	A1	

## Universal Scientific Industrial Co., Ltd.



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#### 13. ESD LEVEL

Note:

1. Surface Resistivity:

Interior:  $10^9 \sim 10^{11} \Omega / \text{SQUARE}$ 

EXTERIOR:  $10^8 \sim 10^{12} \Omega / \text{SQUARE}$ 

2. Dimension:475\*420mm

3. Tolerance:+5,0mm

4. Color:

Background: Gray

Text: Red

Length leader / trailer tape:

Leader tape: ≥550mm which includes ≥100mm of carrier tape with empty compartments and

covered with tape; remaining part might be of cover tape only.

Trailer tape: ≥160mm with empty compartments and covered with tape.

#### **NOTES:**

1. Material: Conductive Polystyrene (Recycle)

2. Color: Black

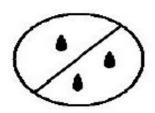
3. Surface resistance: 10 Ohms/square 以下.

Cumulative tolerance per 10 pictches(P<sub>0</sub>) is ±0.2mm.

A<sub>0</sub> & B<sub>0</sub> are measured on the plane by 0.3mm above the bottom of the pocket.

- 4. K<sub>0</sub> is measured from the Inside bottom of the pocket to the top surface of the carrier.
- 5. Pocket position relative to sprocket hold is measured as true position of pocket, not sprocket hold.

#### MSL LEVEL / STORAGE CONDITION 14.



# This bag contains MOISTURE-SENSITIVE DEVICES

	LEVEL
	3
IT	Blank, see ajar cent

- 1. Calculated Shelf life in sealed bag: 12 months at < 40°C and < 90%Relative humidity (RH)
- 2. Peak package body temperature 250
  If Blank, see adjace
- 3. After bag is opened, Devices that will be subjected to reflow solder or other high temperature process must (a) Mounted within: 168 hrs. Of factory conditions ≤ 30°C/60% RH, OR If Blank, see adjacent bar code label
  - (b) Stored at < 10 CRH.</p>
- 4. Devices require bake, before mounting, it:
  - (a) Humidity indicator Card is >10% when read at 23±5°C
  - (b) 3a or 3b not met.
- If baking is required, Devices may be baked for 24 hrs at 125±5℃ Note: If device containers cannot be subjected to high temperature

Or shorter bake times are desired. Reference IPC/JEDEC J-STD-033 for bake procedure

Date: Note: Level and body temperature defined by IPC/JEDEC J-STD-020 If Blank, see adjacent bar code label Bag Seal Date:

Life cycle: 2 years

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For Additional information, please contact the following:

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